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(54) **HIGH ELECTRON MOBILITY TRANSISTOR
AND METHOD FOR FABRICATING THE
SAME**

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(57) **ABSTRACT**

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A method for fabricating a high electron mobility transistor (HEMT) includes the steps of first forming a buffer layer on a substrate, forming a barrier layer on the buffer layer, forming a p-type semiconductor layer on the barrier layer, forming a first layer having a negative charge region adjacent to one side of the p-type semiconductor layer, and then forming a second layer having a positive charge region adjacent to another side of the p-type semiconductor layer.

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